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<u>Atmel</u> AT28LV64B-20JI

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Features

- Single 3.3V ± 10% Supply
- **Hardware and Software Data Protection**
- Low-power Dissipation
 - 15 mA Active Current
 - 20 µA CMOS Standby Current
- Fast Read Access Time 200 ns
- **Automatic Page Write Operation**
 - Internal Address and Data Latches for 64 Bytes
 - Internal Control Timer
- Fast Write Cycle Times
 - Page Write Cycle Time: 10 ms Maximum
 - 1 to 64 Byte Page Write Operation
- DATA Polling for End of Write Detection
- **High-reliability CMOS Technology**
 - Endurance: 100,000 Cycles
 - Data Retention: 10 Years
- JEDEC Approved Byte-wide Pinout
- **Commercial and Industrial Temperature Ranges**

Description

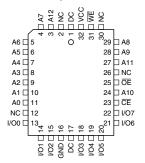
The AT28LV64B is a high-performance electrically erasable programmable read only memory (EEPROM). Its 64K of memory is organized as 8,192 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 200 ns with power dissipation of just 54 mW. When the device is deselected, the CMOS standby current is less than 20 µA.

(continued)

Pin Configurations

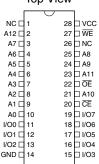
Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect
DC	Don't Connect

PLCC Top View

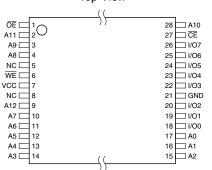


Note: PLCC package pins 1 and 17 are DON'T CONNECT.





TSOP Top View





64K (8K x 8) Low-voltage **Parallel EEPROM** with Page Write and Software **Data Protection**

AT28LV64B







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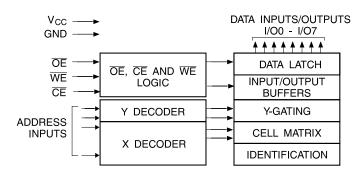


The AT28LV64B is accessed like a static RAM for the read or write cycle without the need for external components. The device contains a 64 byte page register to allow writing of up to 64 bytes simultaneously. During a write cycle, the addresses and 1 to 64 bytes of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by DATA polling of

I/O7. Once the end of a write cycle has been detected a new access for a read or write can begin.

Atmel's AT28LV64B has additional features to ensure high quality and manufacturability. A software data protection mechanism guards against inadvertent writes. The device also includes an extra 64 bytes of EEPROM for device identification or tracking.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including NC Pins) with Respect to Ground0.6V to +6.25V
All Output Voltages with Respect to Ground0.6V to V _{CC} + 0.6V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability



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AT28LV64B

Device Operation

READ: The AT28LV64B is accessed like a static RAM. When $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are low and $\overline{\text{WE}}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state when either $\overline{\text{CE}}$ or $\overline{\text{OE}}$ is high. This dualline control gives designers flexibility in preventing bus contention in their systems.

BYTE WRITE: A low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and \overline{OE} high initiates a write cycle. The address is latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of t_{WC} , a read operation will effectively be a polling operation

PAGE WRITE: The page write operation of the AT28LV64B allows 1 to 64 bytes of data to be written into the device during a single internal programming period. A page write operation is initiated in the same manner as a byte write; the first byte written can then be followed by 1 to 63 additional bytes. Each successive byte must be written within 100 μ s (t_{BLC}) of the previous byte. If the t_{BLC} limit is exceeded, the AT28LV64B will cease accepting data and commence the internal programming operation. All bytes during a page write operation must reside on the same page as defined by the state of the A6 to A12 inputs. For each \overline{WE} high to low transition during the page write operation, A6 to A12 must be the same.

The A0 to A5 inputs specify which bytes within the page are to be written. The bytes may be loaded in any order and may be altered within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

DATA POLLING: The AT28LV64B features DATA Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data to be presented on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next write cycle may begin. DATA Polling may begin at anytime during the write cycle.

TOGGLE BIT: In addition to DATA Polling, the AT28LV64B provides another method for determining the end of a write cycle. During the write operation, successive attempts to

read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop toggling and valid data will be read. Reading the toggle bit may begin at any time during the write cycle.

DATA PROTECTION: If precautions are not taken, inadvertent writes may occur during transitions of the host system power supply. Atmel has incorporated both hardware and software features that will protect the memory against inadvertent writes.

HARDWARE PROTECTION: Hardware features protect against inadvertent writes to the AT28LV64B in the following ways: (a) V_{CC} power-on delay—once V_{CC} has reached 1.8V (typical) the device will automatically time out 10 ms (typical) before allowing a write; (b) write inhibit—holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits write cycles; and (c) noise filter—pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a write cycle.

SOFTWARE DATA PROTECTION: A software-controlled data protection feature has been implemented on the AT28LV64B. Software data protection (SDP) helps prevent inadvertent writes from corrupting the data in the device. SDP can prevent inadvertent writes during power-up and power-down as well as any other potential periods of system instability.

The AT28LV64B can only be written using the software data protection feature. A series of three write commands to specific addresses with specific data must be presented to the device before writing in the byte or page mode. The same three write commands must begin each write operation. All software write commands must obey the page mode write timing specifications. The data in the 3-byte command sequence is not written to the device; the addresses in the command sequence can be utilized just like any other location in the device.

Any attempt to write to the device without the 3-byte sequence will start the internal write timers. No data will be written to the device; however, for the duration of t_{WC} , read operations will effectively be polling operations.

DEVICE IDENTIFICATION: An extra 64 bytes of EEPROM memory are available to the user for device identification. By raising A9 to 12V \pm 0.5V and using address locations 7FC0H to 7FFFH, the additional bytes may be written to or read from in the same manner as the regular memory array.



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DC and AC Operating Range

		AT28LV64B-20	AT28LV64B-25
Operating	Com.	0°C - 70°C	0°C - 70°C
Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C
V _{CC} Power Supply		3.3V ± 10%	3.3V ± 10%

Operating Modes

Mode	CE	ŌĒ	WE	I/O
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	Х	High Z
Write Inhibit	Х	Х	V _{IH}	
Write Inhibit	Х	V _{IL}	Х	
Output Disable	Х	V _{IH}	Х	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH} .

2. Refer to AC Programming Waveforms.

3. $V_H = 12.0V \pm 0.5V$.

DC Characteristics

Symbol	Parameter	Condition		Min	Max	Units
ILI	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC} + 1V$			10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$	$V_{I/O} = 0V \text{ to } V_{CC}$		10	μΑ
1	V Standby Cymrant CMOS	$\overline{CE} = V_{CC} - 0.3V$ to	Com.		20	μΑ
I _{SB}	V _{CC} Standby Current CMOS	$V_{CC} + 1V$	Ind.		50	μΑ
I _{cc}	V _{CC} Active Current	f = 5 MHz; I _{OUT} = 0 m	A		15	mA
V _{IL}	Input Low Voltage				0.6	V
V _{IH}	Input High Voltage			2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 1.6 mA			0.45	V
V _{OH}	Output High Voltage	I _{OH} = -100 μA		2.0		V

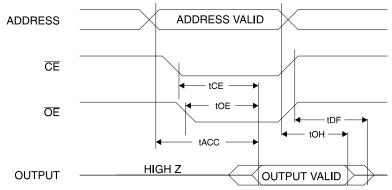
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AT28LV64B

AC Read Characteristics

		AT28L\	AT28LV64B-20		AT28LV64B-25		
Symbol	Parameter	Min	Max	Min	Max	Units	
t _{ACC}	Address to Output Delay		200		250	ns	
t _{CE} ⁽¹⁾	CE to Output Delay		200		250	ns	
t _{OE} ⁽²⁾	OE to Output Delay	0	80	0	100	ns	
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE to Output Float	0	55	0	60	ns	
t _{OH}	Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first	0		0		ns	

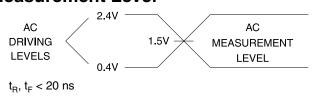
AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



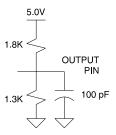
Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} - t_{CE} after the address transition without impact on t_{ACC} .

- 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
- 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Max	Units	Conditions
C _{IN}	4	6	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	V _{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.



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AC Write Characteristics

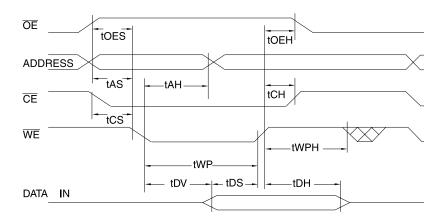
Symbol	Parameter	Min	Max	Units
t_{AS}, t_{OES}	Address, OE Set-up Time	0		ns
t _{AH}	Address Hold Time	100		ns
t _{CS}	Chip Select Set-up Time	0		ns
t _{CH}	Chip Select Hold Time	0		ns
t _{WP}	Write Pulse Width (WE or CE)	200		ns
t _{DS}	Data Set-up Time	100		ns
t _{DH} , t _{OEH}	Data, $\overline{\text{OE}}$ Hold Time	0		ns
t _{DV}	Time to Data Valid	NR ⁽¹⁾		
t _{WPH}	Write Pulse Width High	100		ns

Notes: 1. NR = No Restriction

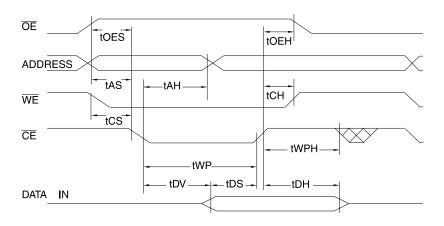
2. All byte write operations must be preceded by the SDP command sequence.

AC Write Waveforms

WE Controlled



CE Controlled



AT28LV64B

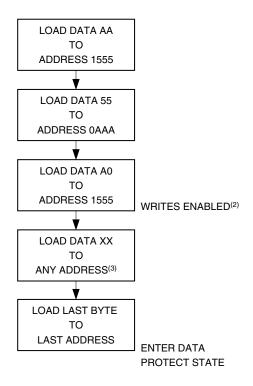


AT28LV64B

Page Mode Characteristics

Symbol	Parameter	Min	Max	Units
t _{WC}	Write Cycle Time		10	ms
t _{AS}	Address Set-up Time	0		ns
t _{AH}	Address Hold Time	100		ns
t _{DS}	Data Set-up Time	100		ns
t _{DH}	Data Hold Time	0		ns
t _{WP}	Write Pulse Width	200		ns
t _{BLC}	Byte Load Cycle Time		100	μs
t _{WPH}	Write Pulse Width High	100		ns

Write Algorithm⁽¹⁾



Notes for software program code:

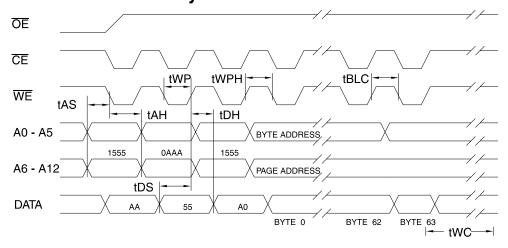
- 1. Data Format: I/O7 I/O0 (Hex); Address Format: A12 A0 (Hex).
- 2. Data protect state will be re-activated at the end of the write cycle.
- 3. 1 to 64 bytes of data are loaded.



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Software Data Protection Write Cycle Waveforms(1)(2)(3)



Notes: 1. A0 - A12 must conform to the addressing sequence for the first three bytes as shown above.

- 2. A6 through A12 must specify the same page address during each high to low transition of WE (or CE) after the software code has been entered.
- 3. $\overline{\text{OE}}$ must be high only when $\overline{\text{WE}}$ and $\overline{\text{CE}}$ are both low.

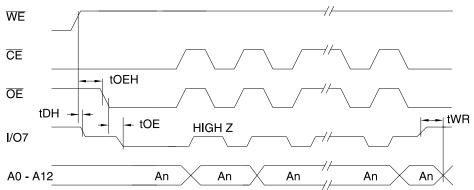
Data Polling Characteristics(1)

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	0			ns
t _{OEH}	OE Hold Time	0			ns
t _{OE}	OE to Output Delay ⁽²⁾				ns
t _{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Read Characteristics.

Data Polling Waveforms





AT28LV64B

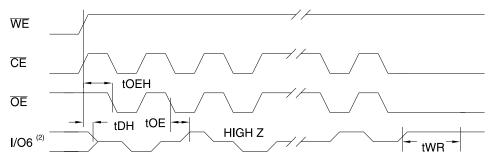
Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	\overline{OE} to Output Delay ⁽²⁾				ns
t _{OEHP}	OE High Pulse	150			ns
t _{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Read Characteristics.

Toggle Bit Waveforms



Notes: 1. Toggling either \overline{OE} or \overline{CE} or both \overline{OE} and \overline{CE} will operate toggle bit.

- 2. Beginning and ending state of I/O6 will vary.
- 3. Any address location may be used, but the address should not vary.



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Ordering Information⁽¹⁾

t _{ACC}	I _{cc}	(mA)			
(ns)	Active	Standby	Ordering Code	Package	Operation Range
200	15	0.05	AT28LV64B-20JC	32J	Commercial
			AT28LV64B-20PC	28P6	(0°C to 70°C)
			AT28LV64B-20SC	28S	
			AT28LV64B-20TC	28T	
	15	0.05	AT28LV64B-20JI	32J	Industrial
			AT28LV64B-20PI	28P6	(-40°C to 85°C)
			AT28LV64B-20SI	28S	
			AT28LV64B-20TI	28T	
250	15	0.05	AT28LV64B-25JC	32J	Commercial
			AT28LV64B-25PC	28P6	(0°C to 70°C)
			AT28LV64B-25SC	28S	
			AT28LV64B-25TC	28T	
	15	0.05	AT28LV64B-25JI	32J	Industrial
			AT28LV64B-25PI	28P6	(-40°C to 85°C)
			AT28LV64B-25SI	28S	
			AT28LV64B-25TI	28T	

Note: 1. See Valid Part Number table below.

Valid Part Numbers

The following table lists standard Atmel products that can be ordered.

Device Numbers	Speed	Package and Temperature Combinations
AT28LV64B	20	JC, JI, PC, PI, SC, SI, TC, TI
AT28LV64B	25	JC, JI, PC, PI, SC, SI, TC, TI

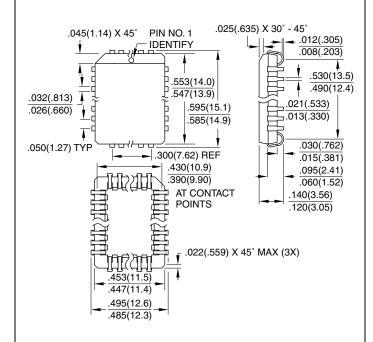
Package Type		
32J	32-lead, Plastic J-leaded Chip Carrier (PLCC)	
28P6	28-pin, 0.600" Wide, Plastic Dual Inline Package (PDIP)	
28S	28-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)	
28T	28-lead, Plastic Thin Small Outline Package (TSOP)	



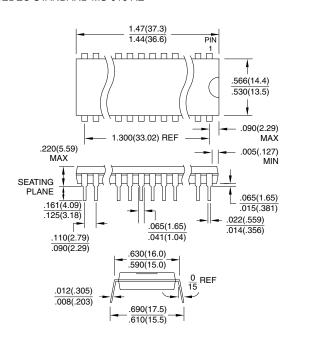
AT28LV64B

Packaging Information

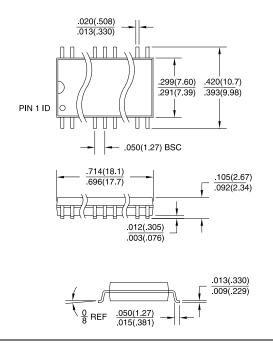
32J, 32-lead, Plastic J-leaded Chip Carrier (PLCC) Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-016 AE



28P6, 28-pin, 0.600" Wide, Plastic Dual In-Line Package (PDIP) Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-016 AE

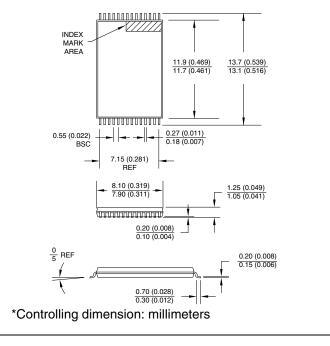


28S, 28-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC) Dimensions in Inches and (Millimeters)



28T, 28-lead, Plastic Thin Small Outline Package (TSOP)

Dimensions in Millimeters and (Inches)*





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Atmel Headquarters

Corporate Headquarters

2325 Orchard Parkway San Jose, CA 95131 TEL (408) 441-0311 FAX (408) 487-2600

Europe

Atmel U.K., Ltd.
Coliseum Business Centre
Riverside Way
Camberley, Surrey GU15 3YL
England
TEL (44) 1276-686-677
FAX (44) 1276-686-697

Asia

Atmel Asia, Ltd.
Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimhatsui
East Kowloon
Hong Kong
TEL (852) 2721-9778
FAX (852) 2722-1369

Japan

Atmel Japan K.K. 9F, Tonetsu Shinkawa Bldg. 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan TEL (81) 3-3523-3551 FAX (81) 3-3523-7581

Atmel Operations

Atmel Colorado Springs

1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 TEL (719) 576-3300 FAX (719) 540-1759

Atmel Rousset

Zone Industrielle 13106 Rousset Cedex France TEL (33) 4-4253-6000 FAX (33) 4-4253-6001

Fax-on-Demand

North America: 1-(800) 292-8635 International: 1-(408) 441-0732

e-mail

literature@atmel.com

Web Site

http://www.atmel.com

BBS

1-(408) 436-4309

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